



# Product data sheet

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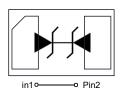


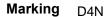
PTVSHC2EN4V5B-MS

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#### DFN1610-2L





#### Feature

- 1200W Peak pulse power per line (t<sub>P</sub> = 8/20µs)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
  ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

#### **Applications**

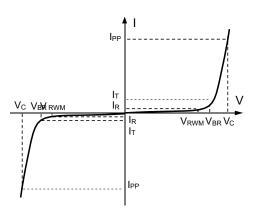
- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- > Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- > Peripherals
- MP3 players

### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil
- > Device meets MSL 3 requirements

## **Electronics Parameter**

Symbol	Parameter	
VRWM	Peak Reverse Working Voltage	
IR	Reverse Leakage Current @ V <sub>RWM</sub>	
V <sub>BR</sub>	Breakdown Voltage @ I⊤	
lτ	Test Current	
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P <sub>PP</sub>	Peak Pulse Power	
CJ	Junction Capacitance	







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## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Zener Voltage	Vz	I <sub>ZT</sub> = 5mA		5.1		V
Reverse Working Voltage <sup>(1)</sup>	VRWM				4.5	V
Breakdown Voltage(PIN1~PIN2)	V <sub>BR</sub>	It=1mA	4.6	5.2	6.1	V
Reverse Leakage Current(PIN1~PIN2)	IR	V <sub>RWM</sub> =4.5V			0.2	μA
Clamping Voltage(PIN1~PIN2)	Vc	I <sub>PP</sub> =20A t <sub>P</sub> = 8/20µs		6.5	8	V
Clamping Voltage(PIN1~PIN2)	Vc	I <sub>PP</sub> =45A t <sub>P</sub> = 8/20µs		7.5	9	V
Clamping Voltage(PIN1~PIN2)	Vc	I <sub>PP</sub> =90A t <sub>P</sub> = 8/20µs		9.5	12	V
Clamping Voltage(PIN1~PIN2)	Vc	I <sub>PP</sub> =130A t <sub>P</sub> = 8/20µs		10	13	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		400	500	pF

Note 1:  $V_{RWM}$  is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over  $V_{RWM}$ , ESD will change to other state.

# Absolute maximum rating@25℃

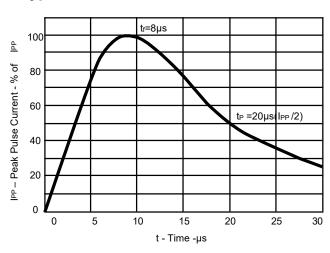
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_P = 8/20\mu S$ )	P <sub>pp</sub>	1200	w
Total Device Dissipation FR-5 Board	PD	500	mW
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	Tstg	-55 to +150	°C

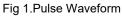


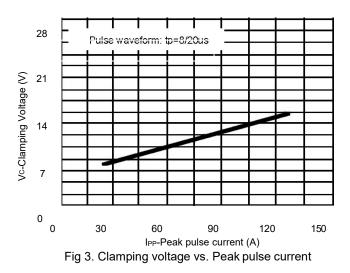


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# **Typical Characteristics**







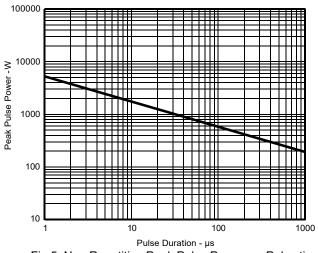
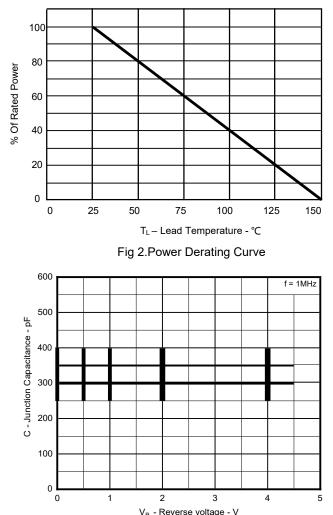
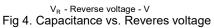


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time



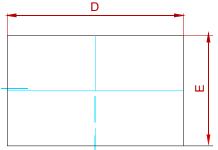


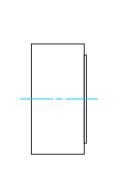


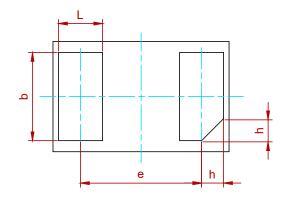
# PTVSHC2EN4V5B-MS

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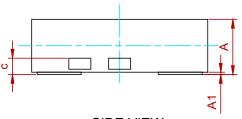
PACKAGE MECHANICAL DATA







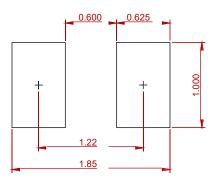
TOP VIEW



BOTTOM VIEW

Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
A	0.45	0.50	0.55	
A1	0.00	0.02	0.05	
с	0.15 Ref.			
b	0.75	0.80	0.85	
L	0.35	0.40	0.45	
D	1.55	1.60	1.65	
E	0.95	1.00	1.05	
е	1.10 BSC			
h	0.20 Ref.			

### Recommend PCB Layout (Unit: mm)



#### Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

# **REEL SPECIFICATION**

P/N	PKG	QTY
PTVSHC2EN4V5B-MS	DFN1610-2L	3000



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